

CHAPTER FIVE

RTL NOR Gate

Digital Electronics.

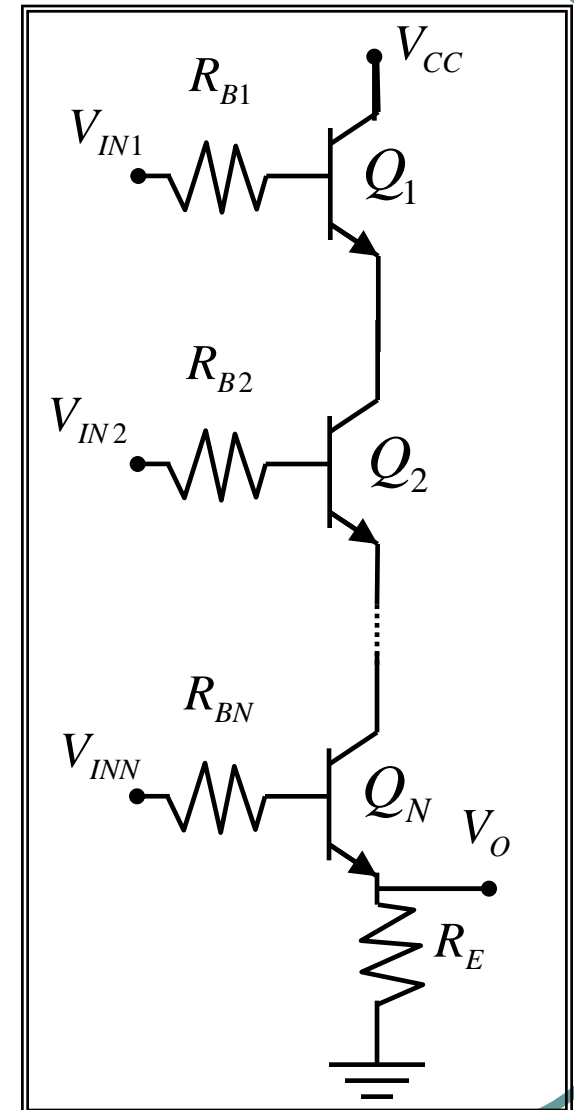
Basic RTL AND Gate

If at least one input less than $V_{BE}(FA)$, then the corresponding Q is off. i.e. $I_E = 0$

$$V_{OL} = 0$$

If ALL inputs are greater than V_{IH} , then the corresponding Q is saturated.

$$V_{OH} = V_{CC} - N \times V_{CE}(sat)$$



RTL With Active Pull-Up Inverter

The object is to increase the fan-out of RTL inverter gate (gives more current).

To accomplish active pull-up:

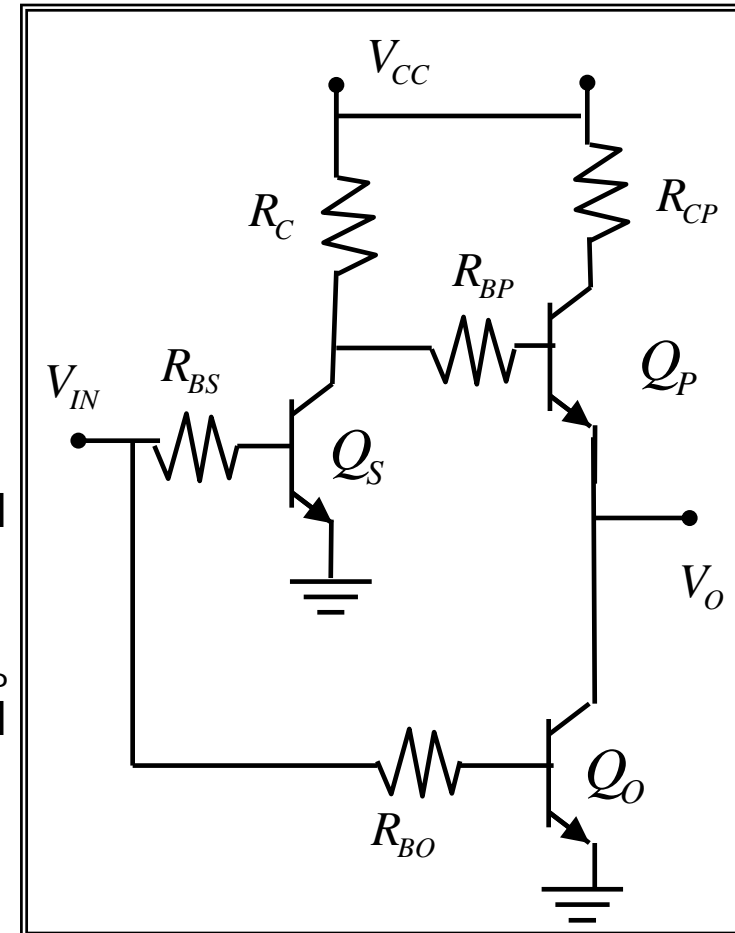
Basic assumptions: *

$$R_{CP} \ll R_C$$

$$R_{CP} \cong 0.1 \times R_C$$

* $R_{BS} = R_{BO}$ and Q_O & Q_S turn ON and OFF simultaneously

* Q_S provides logic inversion for Q_P such that Q_S & Q_P never turn ON simultaneously



RTL With Active Pull-Up Inverter

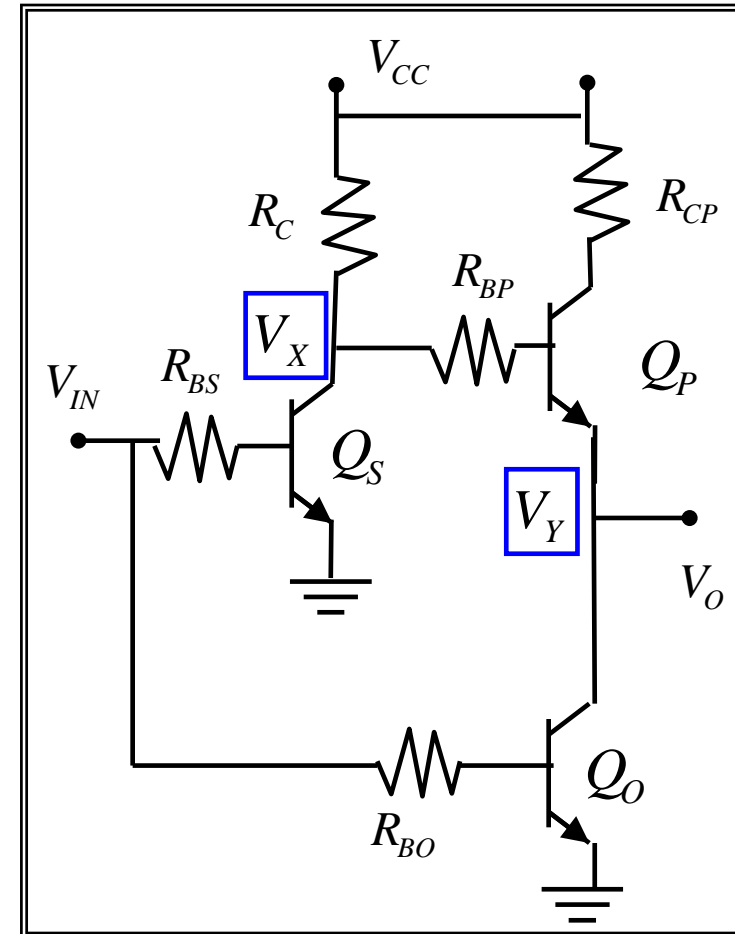
For $V_{IN} \geq V_{INH}$ (Logic High)

Q_O & Q_S are ON (sat) $V_X = V_Y = 0.2V \rightarrow$
 $V_X - V_Y < V_{BEP}(FA)$. i.e. Q_P is cut-off (very
 very large resistance)

For $V_{IN} \leq V_{INL}$ (Logic Low)

Q_O & Q_S are cut-off
 Q_P is ON (sat)

$$V_O = V_{CC} - V_{CE}(sat) - I_{CP}R_{CP}$$

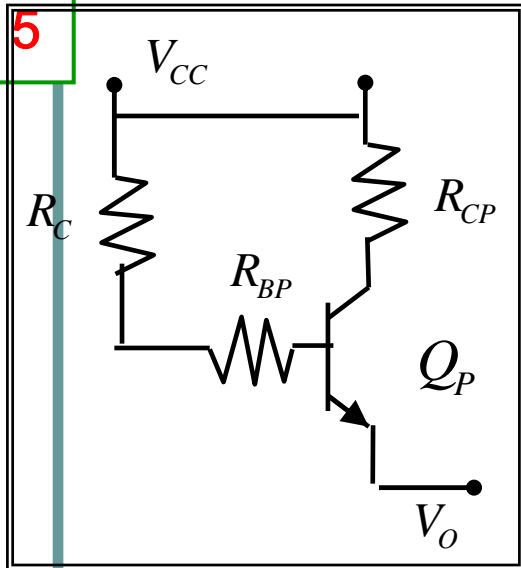


Fan-Out of RTL With Active Pull-Up Inverter

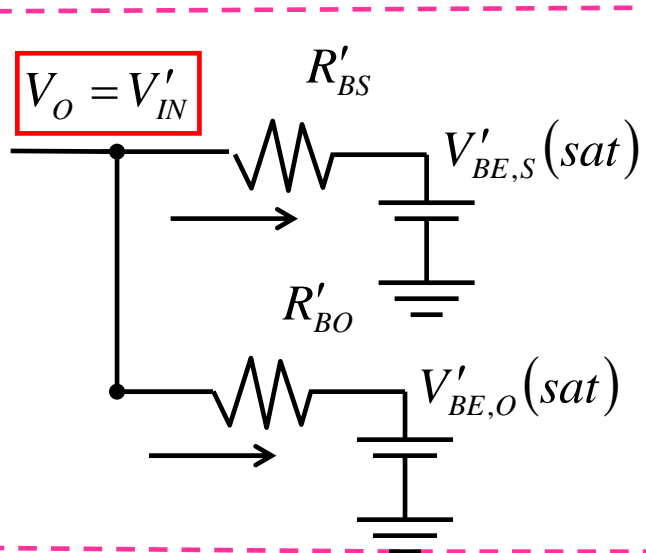
Fan-out is limited by the output high state of the driving gate

Q_O & Q_S are cut-off

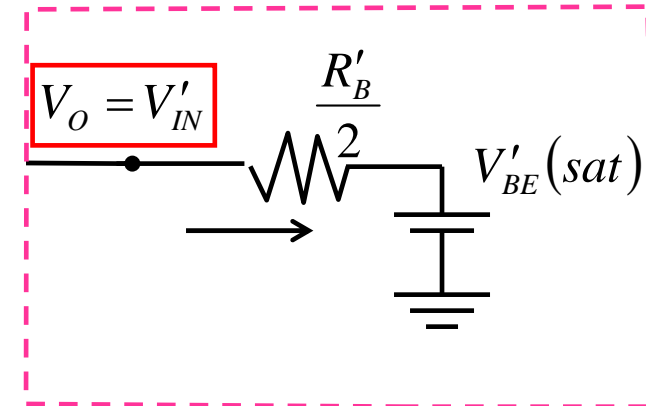
Q_P is ON (sat)



Equivalent cct of driving gate when output is high



Equivalent cct of one load gate when input is high

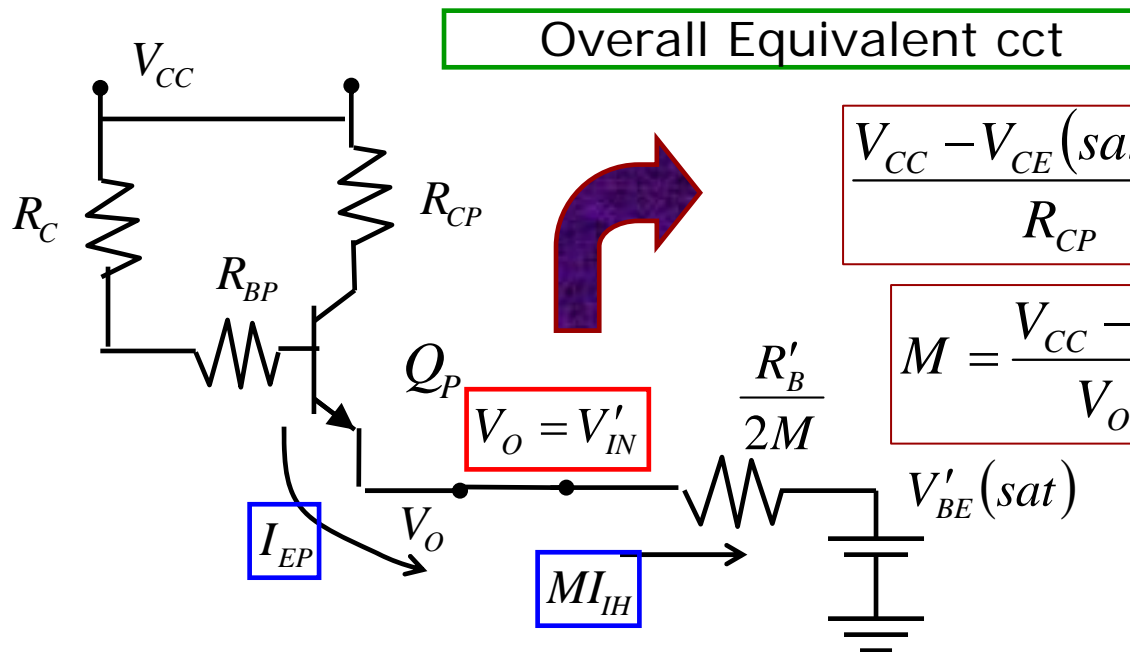


Fan-Out of RTL With Active Pull-Up Inverter

Fan-out is limited by the output high state of the driving gate

Q_O & Q_S are cut-off

Q_P is ON (sat)



$$\frac{V_{CC} - V_{CE}(sat) - V_O}{R_{CP}} = \frac{V_O - V_{BE}(sat)}{R'_B/2M}$$

$$M = \frac{V_{CC} - V_{CE}(sat) - V_O}{V_O - V_{BE}(sat)} \times \frac{R'_B}{2R_{CP}}$$

As M increases, I_{EP} increases, then V_O decreases

Fan-Out of RTL With Active Pull-Up Inverter

The limiting factor for V_O is that it must be sufficient to saturate Q_S' and Q_O' of the load gates.

It is easy to saturate Q_S since its effective load seen by the collector is very large with negligible I_C and I_B since Q_P is cut-off

i.e. to saturate Q_S , we need:

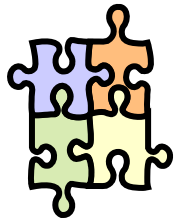
$$V_{OH}(\min) = V_{IH} = V_{BE}(sat) + \frac{R_B}{\beta_F} \left(\frac{V_{CC} - V_{CE,S}(sat)}{R_C} \right) \quad (\text{Proved also in p. 10 of CH.4})$$

Substitute in

$$M = \frac{V_{CC} - V_{CE}(sat) - V_O}{V_O - V_{BE}(sat)} \times \frac{R'_B}{2R_{CP}}$$



Fan-Out of RTL With Active Pull-Up Inverter



Example

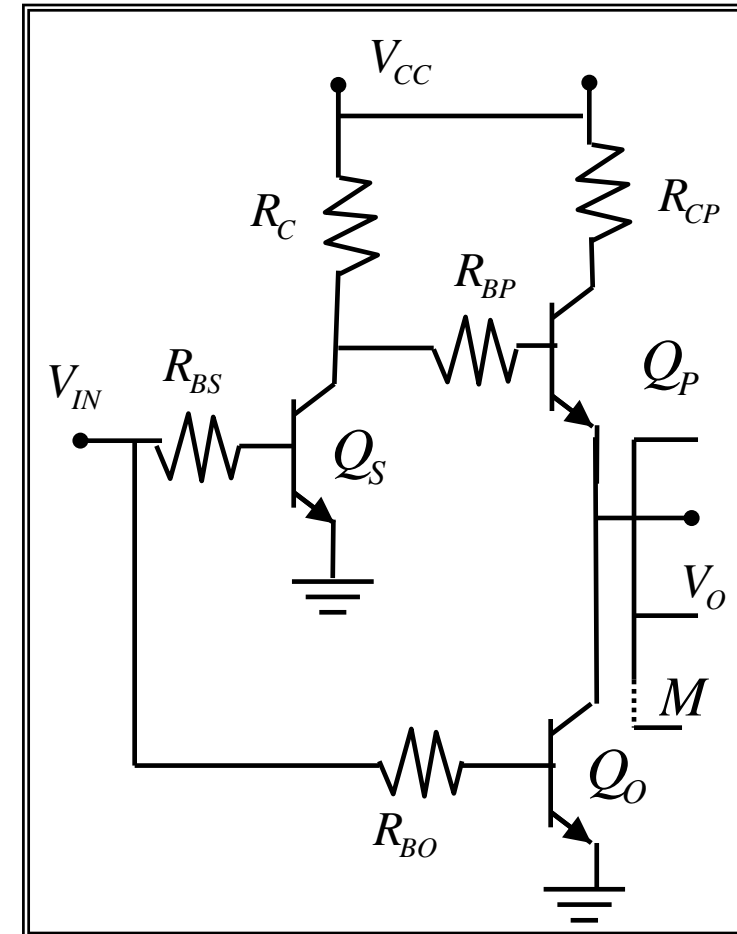
Determine the maximum **fan-out** for driving RTL gate, assuming $V_{CE}(\text{sat})=0.2\text{V}$, $V_{BE}(\text{sat})=0.8\text{V}$, $\beta_F=25$, $V_{CC}=5\text{V}$, $R_C=1\text{k}\Omega$, $R_{BO}=R_{BS}=10\text{k}\Omega$, $R_{CP}=100\Omega$.

Solution

$$V_{OH}(\text{min}) = 0.8 + \frac{10}{25} \left(\frac{5 - 0.2}{1} \right) = 2.7\text{V}$$

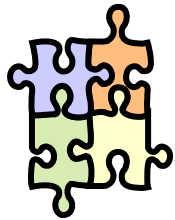
$$M = \frac{5 - 0.2 - 2.7}{2.7 - 0.8} \times \frac{10}{2 \times 0.1} = 55.3$$

$$M = 55$$



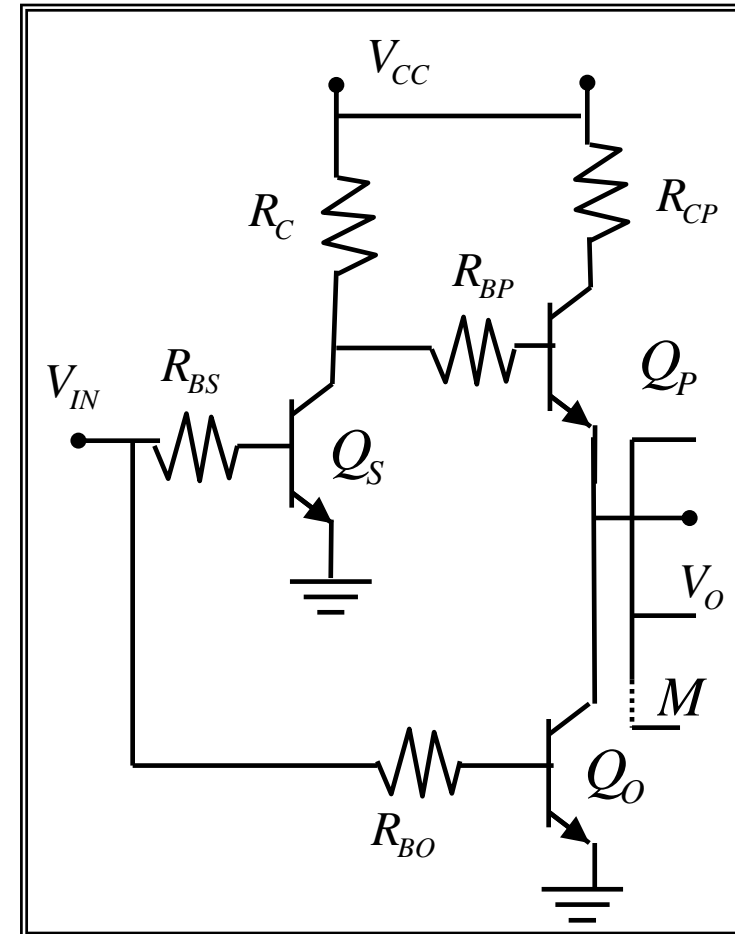
(without pull-up, M was 11. i.e. It increases 500%. See p. 10)

RTL SPICE Simulation

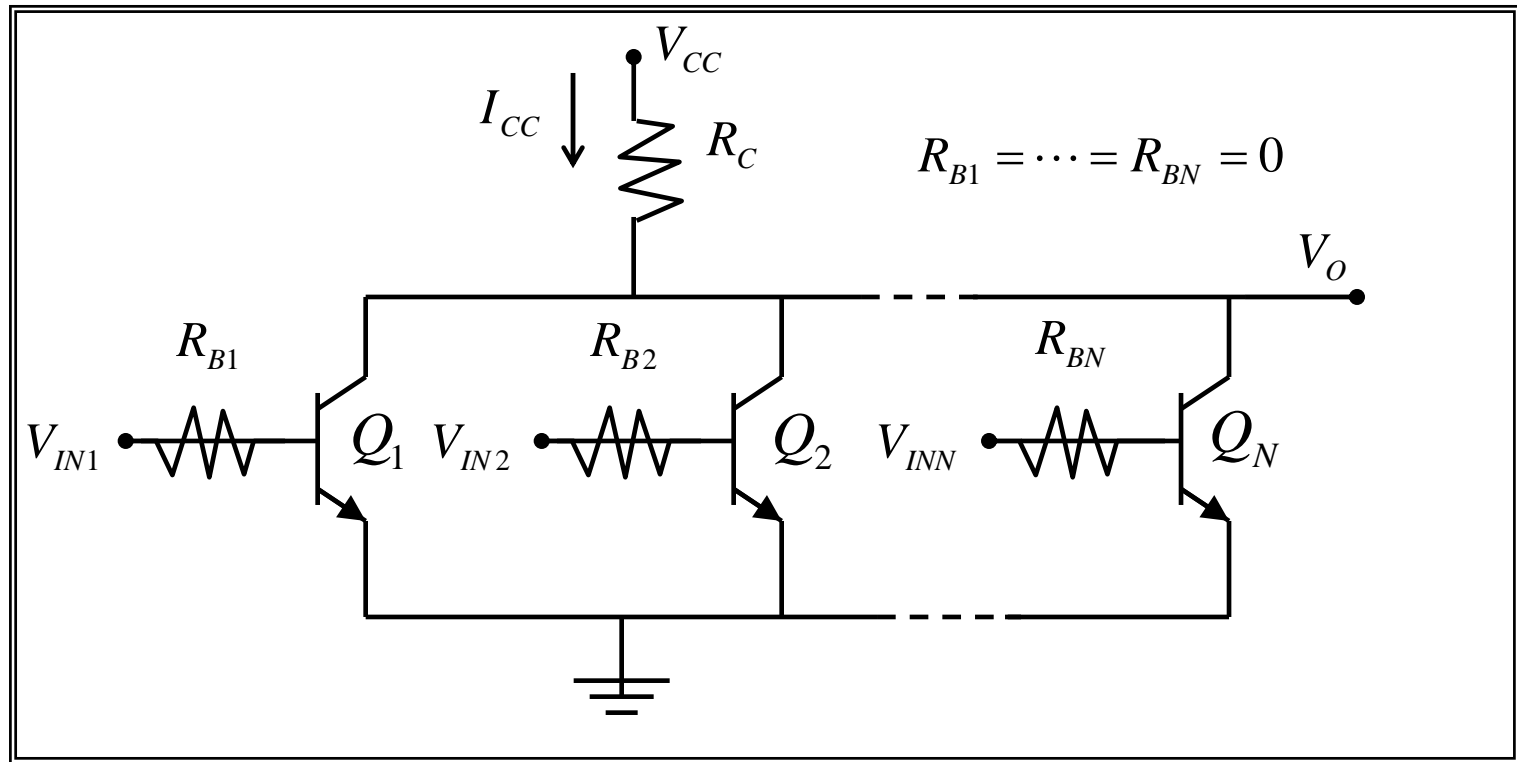


● Example

- *Repeat the last example using PSPICE
- *Plot V_O as a function of V_{IN}
- *Refer to pages 67-68 in the text book.



Direct Coupled Transistor Logic



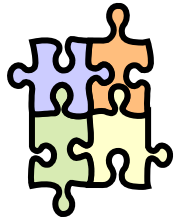
Three-input DCTL NOR gate

Advantage: Reduce the packing density of RTL in integrated circuits form since the base resistors are eliminated

Disadvantage: Current hogging when V_o is at logic high for fan-out greater than one



Direct Coupled Transistor Logic

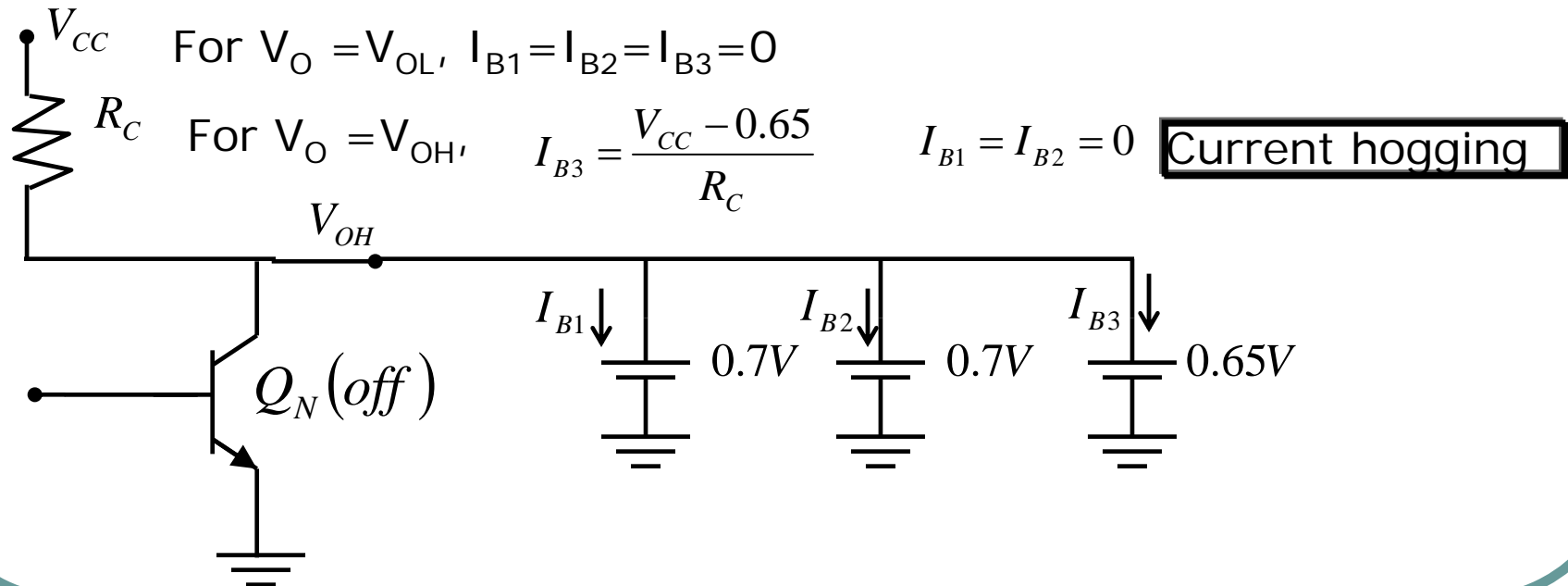


● Example

Consider a DCTL RTL inverter with fan-out be three with $V_{BE1}(FA)=0.7V$, $V_{BE2}(FA)=0.7V$, $V_{BE3}(FA)=0.65V$.

Determine the base current of each load gate for output high state.

● Solution



- HW #5: Solve Problems: 5.8, 5.11, 5.22, 5.24, 5.27, 5.28, 5.29 (hint: neglect I_{BP})

- *Solutions of Prob. 5.24 & 5.27:
On the white board*